



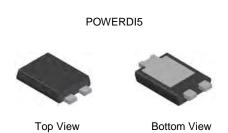
# 40V PNP HIGH GAIN TRANSISTOR POWERDI®

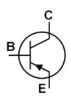
#### **Features**

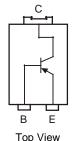
- BV<sub>CEO</sub> > -40V
- I<sub>C</sub> = -3A high Continuous Collector Current
- I<sub>CM</sub> = -6A Peak Pulse Current
- 43% smaller than SOT223; 60% smaller than TO252
- Maximum Height Just 1.1mm
- Rated up to 3.2W
- · Low Saturation, High Gain Transistor,
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: POWERDI5
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.093 grams (approximate)







Pin Out

**Device Schematic** 

**Ordering Information** (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT790AP5-13	DXT790A	13	16	5,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**







**DXT790AP5** 

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	lc	-3	A
Peak Pulse Current	I <sub>CM</sub>	-6	A
Base Current	l <sub>Β</sub>	-0.5	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.2	w	
Power Dissipation	(Note 6)	$P_{D}$	1.7		
	(Note 7)		0.74		
	(Note 5)		39		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ hetaJA}$	75	°C/W	
	(Note 7)	*	169		
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ hetaJL}$	8.9	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

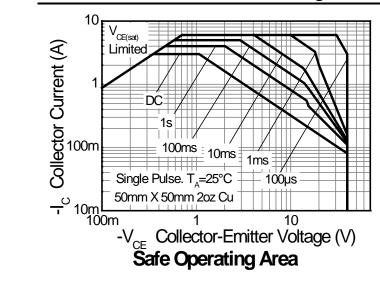
Notes:

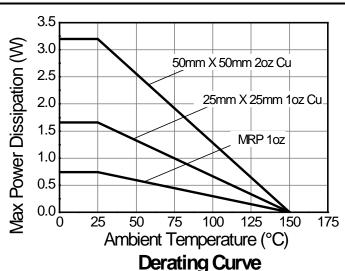
- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
  7. Same as note (5), except the device is mounted on minimum recommended pad (MRP) layout 1oz copper.

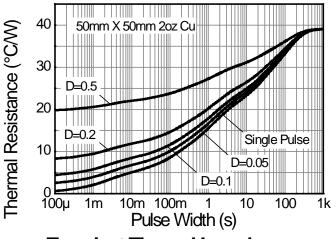
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

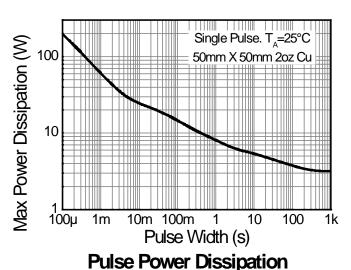


### **Thermal Characteristics and Derating Information**

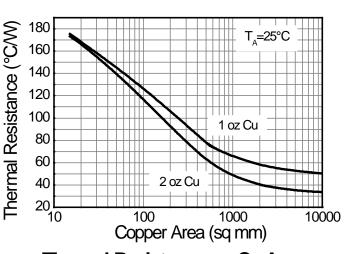








# **Transient Thermal Impedance**



4 T<sub>A</sub>=25°C 2 2 oz Cu 1 oz Cu 1 oz Cu 10 100 1000 10000 Copper Area (sq mm)

Thermal Resistance vs. Cu Area

Power Rating vs. Cu Area

Power Rating (W)



**DXT790AP5** 

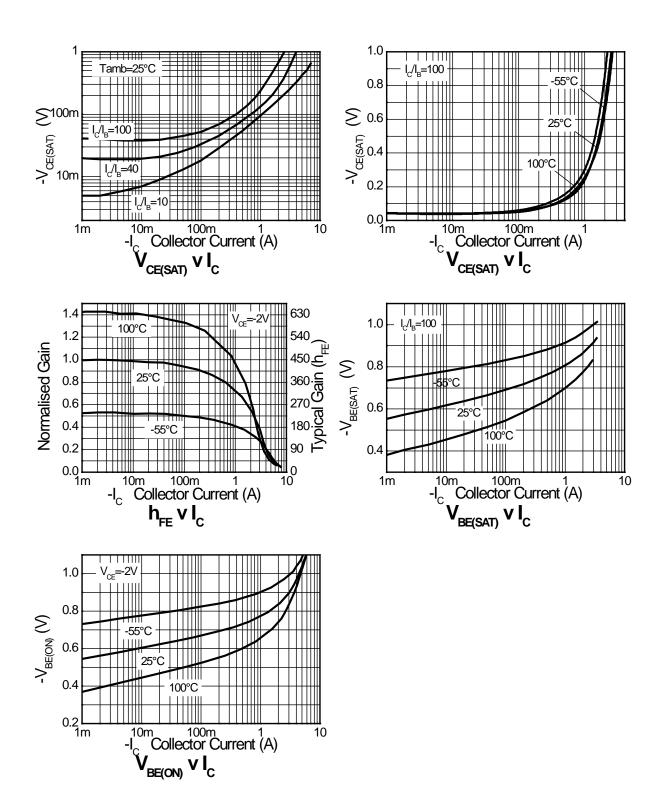
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	_	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	-40	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	_	-20	nA	$V_{CB} = -30V, I_{E} = 0$
Collector Cutoff Current	Ices	_	_	-20	nA	$V_{CB} = -30V, V_{BE} = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-20	nA	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0
ON CHARACTERISTICS (Note 8)						
			_	-170		$I_C = -0.5A$ , $I_B = -5mA$
Collector-Emitter Saturation Voltage	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	_		-350	mV	$I_C = -1A$ , $I_B = -10mA$
Conector-Entitle Saturation Voltage	V <sub>CE(sat)</sub>	_	_	-450	IIIV	$I_C = -2A$ , $I_B = -50mA$
			_	-450		$I_C = -3A$ , $I_B = -300mA$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>			-1.15	V	$I_C = -3A$ , $I_B = -300mA$
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>		_	-1.0	V	$I_C = -3A$ , $V_{CE} = -2V$
		300	_	800		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
		250	_	_		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain	h <sub>FE</sub>	200	_	_	_	$I_C = -1A$ , $V_{CE} = -2V$
		150	_	_		$I_C = -2A$ , $V_{CE} = -2V$
		80	_	_		$I_C = -3A$ , $V_{CE} = -2V$
AC CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	100	_	_	MHz	$I_{C} = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 50MHz
Output Capacitance	Cobo		24		pF	V <sub>CB</sub> = -10V, f = 1MHz
Switching Times	t <sub>on</sub>	_	35		ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V},$
Owntoning rimes	t <sub>off</sub>	_	600	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Notes: 8. Measured under pulsed conditions. Pulse width• 300µs. Duty cycle• 2%.



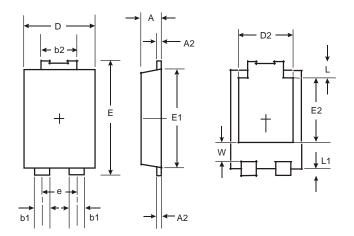
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

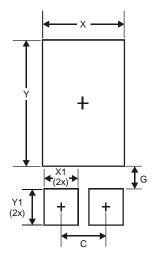
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI5				
Dim	Min	Max		
Α	1.05	1.15		
A2	0.33	0.43		
b1	0.80	0.99		
b2	1.70	1.88		
D	3.90	4.05		
D2	3.054 Typ			
Е	6.40	6.60		
е	1.84 Typ			
E1	5.30 5.45			
E2	3.549 Typ			
L	0.75 0.95			
L1	0.50	0.65		
W	1.10	1.41		
All Dimensions in mm				

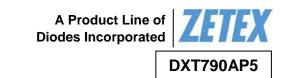
## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Υ	4.860
Y1	1.400





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